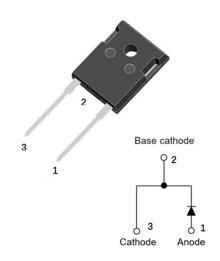


Silicon Carbide Schottky Diode

V_{RRM}	1200V
I _{F (135°C)}	55A
Q _C	209nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

 Package: TO-247AC
 Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_C=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112030NGHD
Reverse voltage (Repetitive peak) @ T _j =25°C	V_{RRM}	V	1200
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1200
Continuous forward current @ T _C =25°C		А	116
Continuous forward current @ T _c =135°C	I _F		55
Continuous forward current @ T _C =160°C			30
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	288
Power Dissipation@ T _C =25°C		W	535
Power Dissipation@ T _C =110°C	Ртот		232
i²t Value@ T _C =25°C ,tp=10ms	∫ i²dt	A ² S	414
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175

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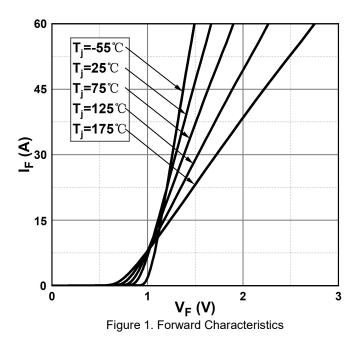
■Electrical Characteristics

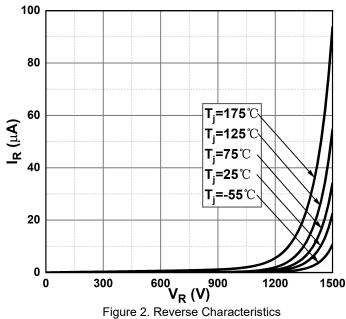
PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V _F	V	I _F =30A, T _j =25°C	1.29	1.55
			I _F =30A, T _j =175°C	1.71	-
Reverse leakage current	I _R	μА	V _R =1200V, T _j =25°C	1	20
			V _R =1200V, T _j =175°C	6	-
Total capacitive charge	Q _C	nC	$\begin{array}{c} V_R = 800V, \ T_j = 25^{\circ}C \ , \\ Q_C = \int_0^{VR} C(V) dV \end{array}$	209	-
Total capacitance	С	pF	V _R =0V, f=1MHZ	3078	-
			V _R =400V, f=1MHZ	197	-
			V _R =800V, f=1MHZ	142	-
Capacitance Stored Energy	Ec	μJ	V _R =800V	54	-

■Thermal Characteristics (T_a=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{\theta J-C}$	°C W	0.28

■Typical Characteristic

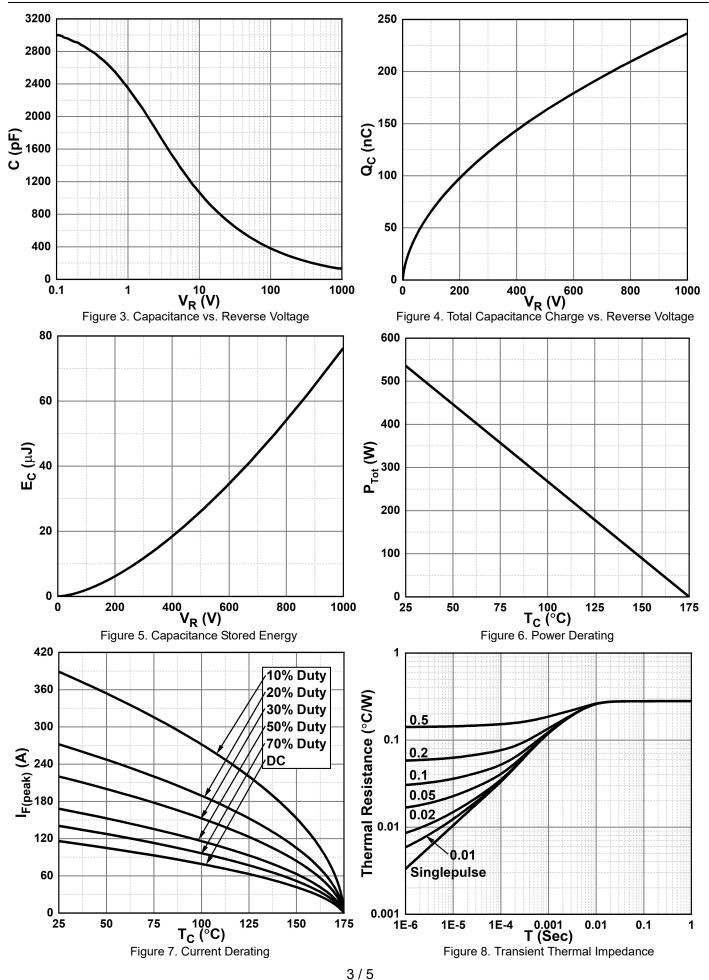




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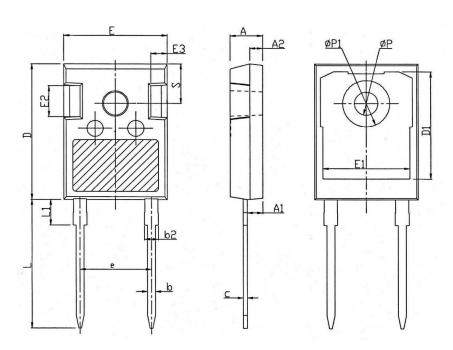






■Outline Dimensions

TO-247AC



TO-247AC				
Dim	Min	Max		
Α	4.80	5.20		
A1	2.21	2.61		
A2	1.85	2.15		
b	1.11	1.36		
b2	1.91	2.21		
С	0.51	0.75		
D	20.70	21.30		
D1	16.25	16.85		
E	15.50	16.10		
E1	13.00	13.60		
E2	4.80	5.20		
E3	2.30	2.70		
е	10.88BSC			
L	19.62	20.22		
L1		4.30		
ΦР	3.40	3.80		
ФР1	-	7.30		
S	6.15BSC			



YJD112030NGHD



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